NCE N-Channel Super Trench II Power MOSFET

Description

The NCEP25N10AD uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.

Application

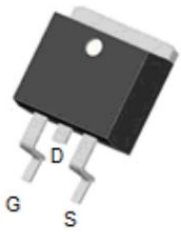
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

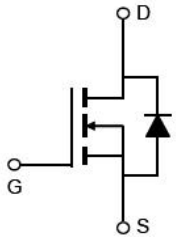
- V_{DS} =100V,I_D =35A
  $R_{DS(ON)}$=21mΩ (typical) @ V_{GS}=10V
  $R_{DS(ON)}$=26mΩ (typical) @ V_{GS}=4.5V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED!
100% ΔVds TESTED!

TO-263-2L



Top View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP25N10AD	NCEP25N10AD	TO-263-2L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	35	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	25	A
Pulsed Drain Current	I_{DM}	140	A
Maximum Power Dissipation	P_D	70	W
Derating factor		0.47	W/℃
Single pulse avalanche energy (Note 1)	E_{AS}	97	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	2.14	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	100		-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.1	1.7	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A	-	21	25	mΩ
		V_{GS}=4.5V, I_D=20A	-	26	30	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=20A	-	19	-	S
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz	-	1317.6	-	PF
Output Capacitance	C_{oss}		-	123.9	-	PF
Reverse Transfer Capacitance	C_{rss}		-	19.3	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=50V,I_D=20A V_{GS}=10V,R_G=3Ω	-	13	-	nS
Turn-on Rise Time	t_r		-	15	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	22	-	nS
Turn-Off Fall Time	t_f		-	6	-	nS
Total Gate Charge	Q_g	V_{DS}=50V,I_D=20A, V_{GS}=10V	-	27.6	-	nC
Gate-Source Charge	Q_{gs}		-	5.5		nC
Gate-Drain Charge	Q_{gd}		-	6.9		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=20A	-		1.2	V
Diode Forward Current	I_S		-	-	35	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F = 20A di/dt = 100A/μs	-	40	-	nS
Reverse Recovery Charge	Qrr		-	85	-	nC

Notes:

1. EAS condition : Tj=25℃,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=175°C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

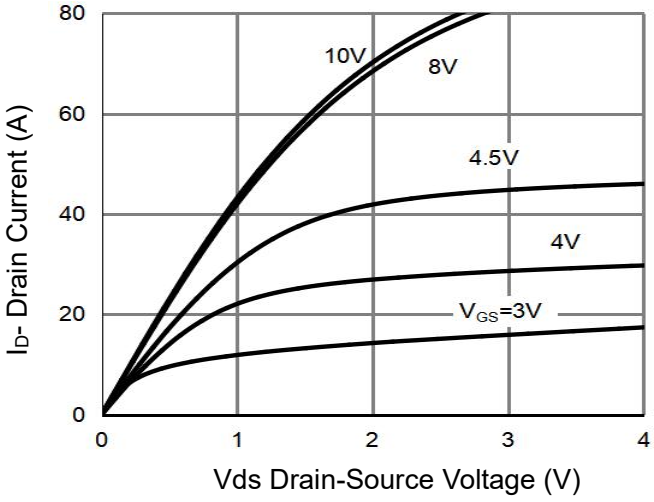


Figure 1 Output Characteristics

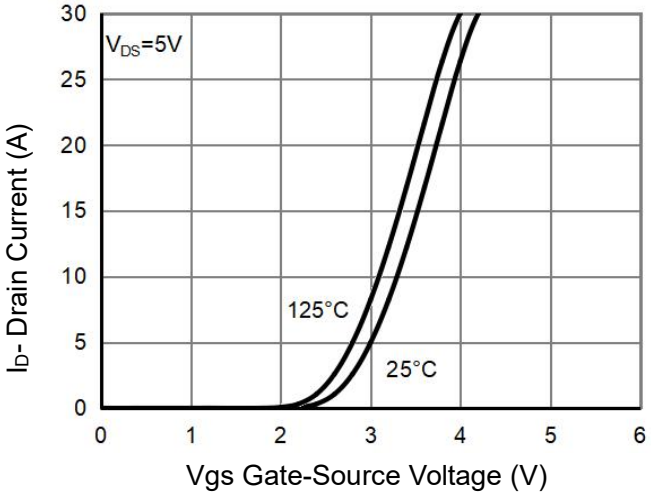


Figure 2 Transfer Characteristics

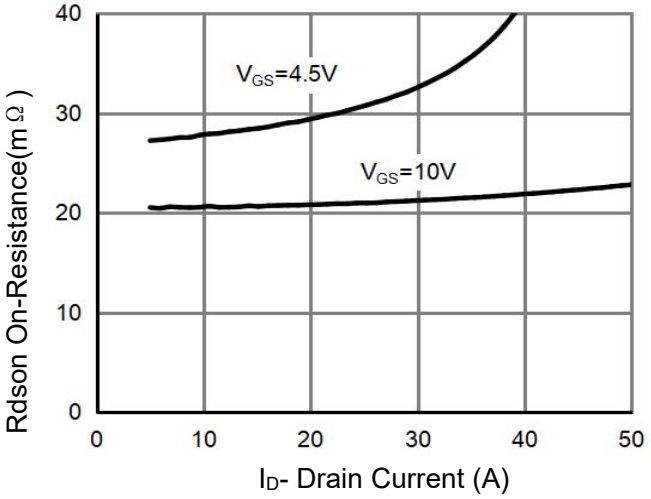


Figure 3 Rdson- Drain Current

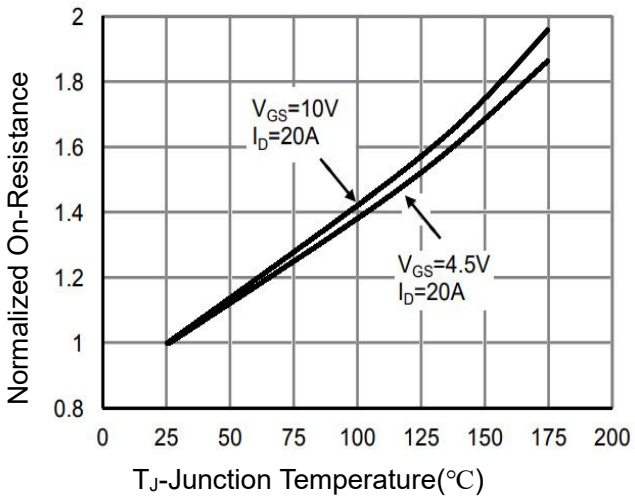


Figure 4 Rdson-Junction Temperature

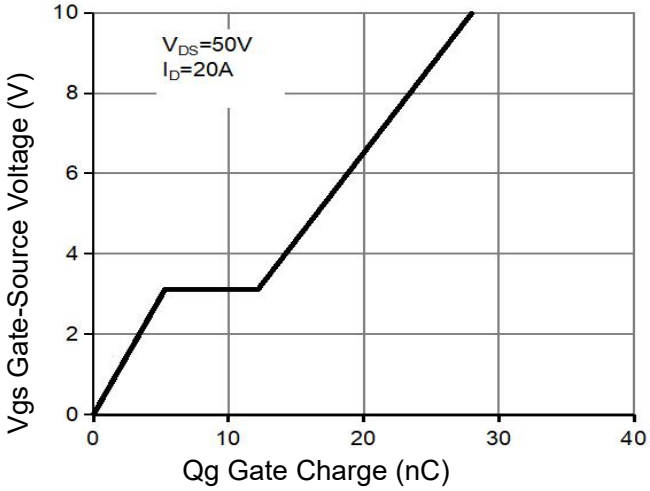


Figure 5 Gate Charge

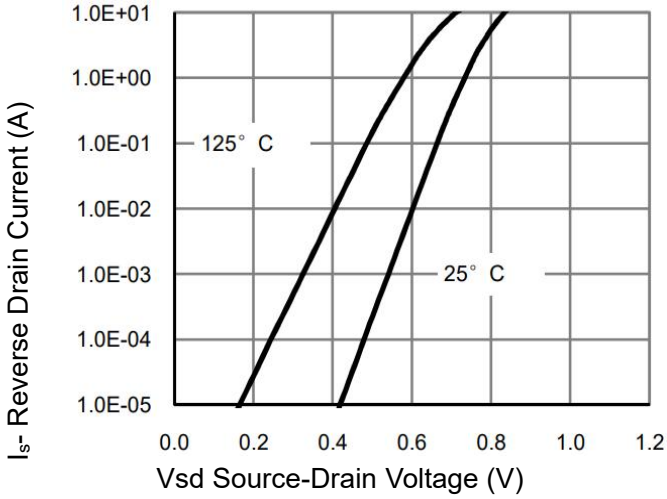


Figure 6 Source- Drain Diode Forward

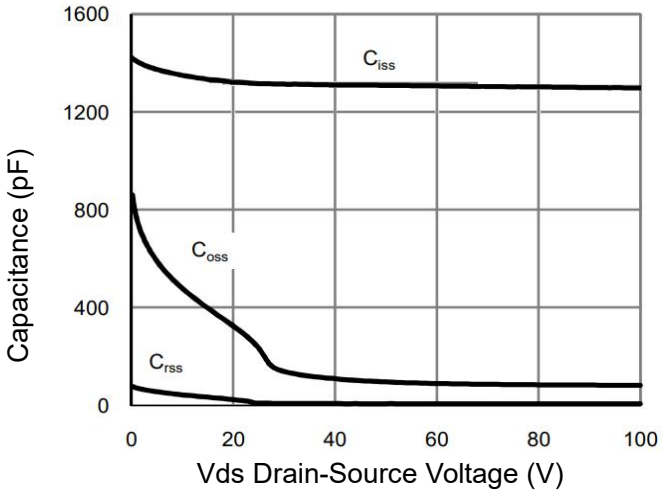


Figure 7 Capacitance vs Vds

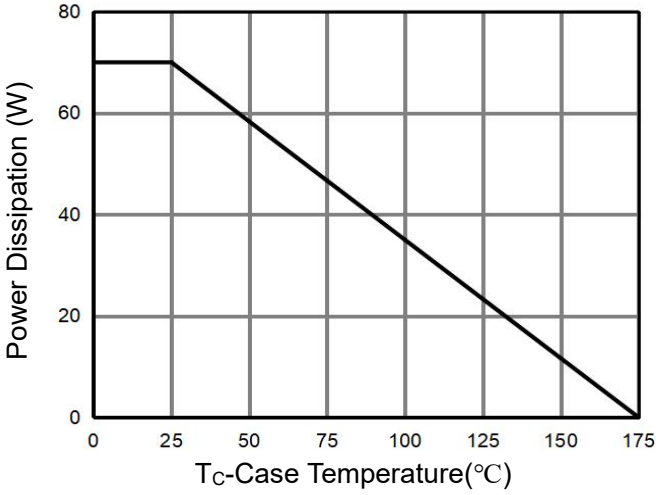


Figure 9 Power De-rating

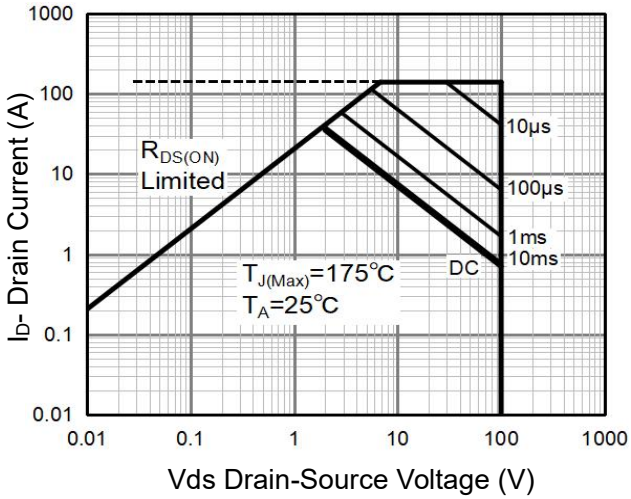


Figure 8 Safe Operation Area (Note3)

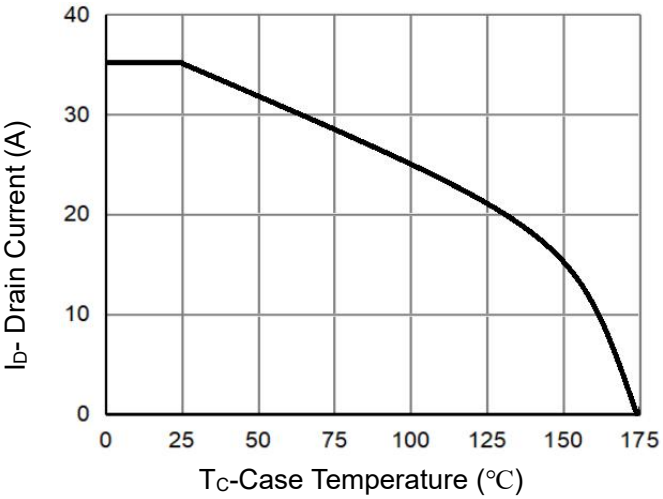


Figure 10 Current De-rating

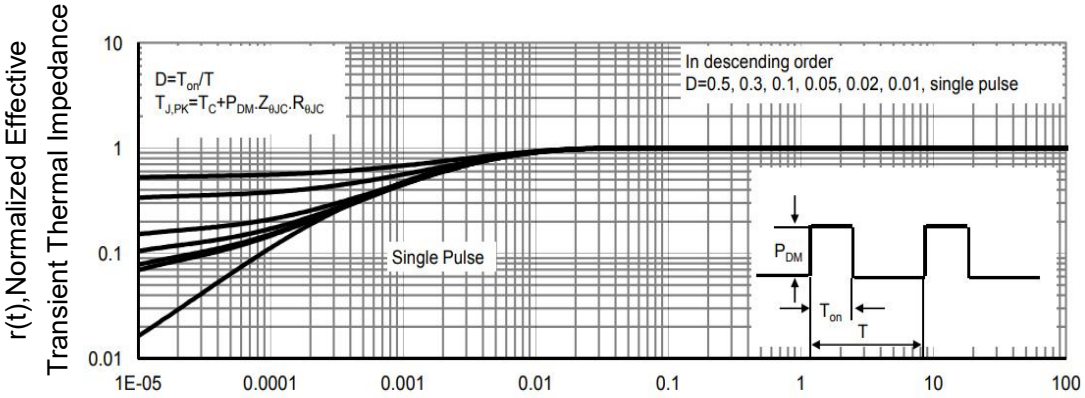
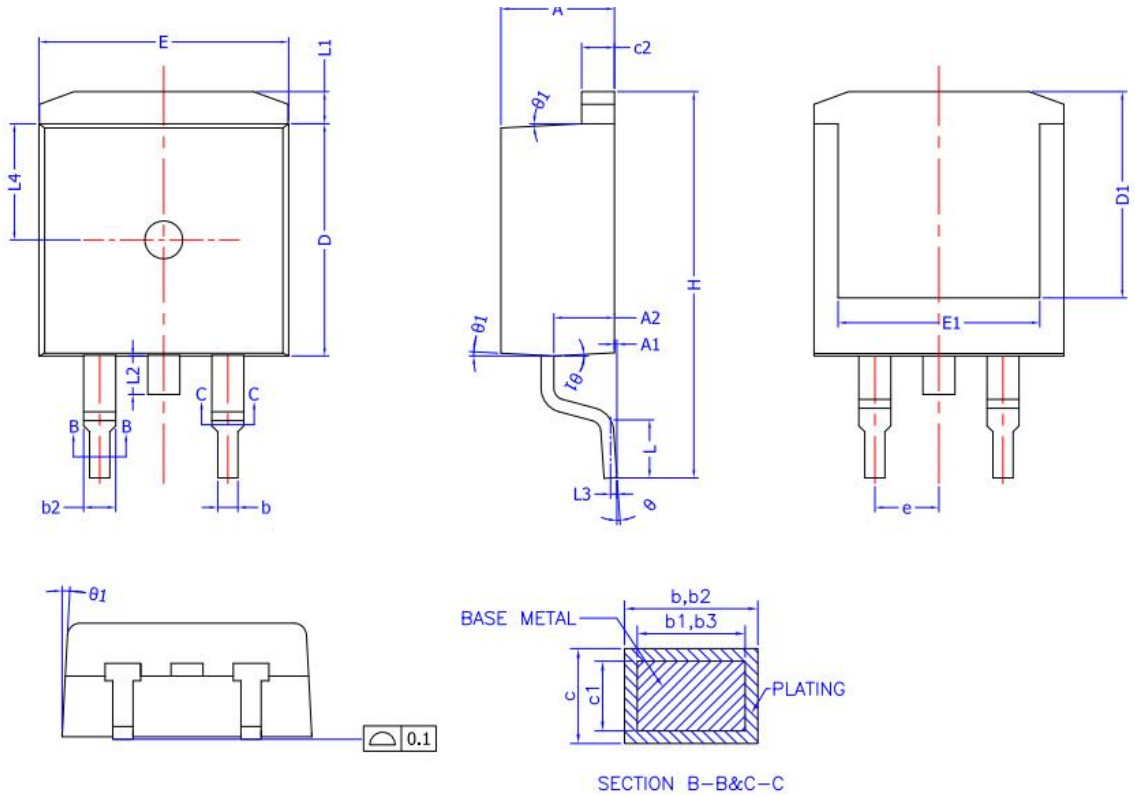


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	0	0.10	0.25
A2	2.20	2.40	2.60
b	0.76	---	0.89
b1	0.75	0.80	0.85
b2	1.23	---	1.37
b3	1.22	1.27	1.32
c	0.47	---	0.60
c1	0.46	0.51	0.56
c2	1.25	1.30	1.35
D	9.10	9.20	9.30
D1	8.00	---	---
E	9.80	9.90	10.00
E1	7.80	---	---
e	2.54 BSC		
H	14.90	15.30	15.70
L	2.00	2.30	2.60
L1	1.17	1.27	1.40
L2	---	---	1.75
L3	0.25BSC		
L4	4.60 REF		
θ	0°	---	8°
θ1	1°	3°	5°

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